



PRO 4|10 EVO

TECHNICAL DATA SHEET

HI-END four-channel Class AB power amplifier

120 W × 4 / 4 Ω 160 W × 4 / 2 Ω

320 W × 2 bridged / 4 Ω

FEATURES

- HI-END Class AB amplification engineered for high power.
- Four-channel operation, with bridged output available at 4 Ω.
- Output stage based on identical N-channel MOSFETs.
- Unregulated power supply with microprocessor-controlled switching.
- Independent input sensitivity adjustment for each channel via DIP switch.
- Microprocessor-controlled fan operation and thermal shutdown protection.
- Two-layer FR4 PCB with 70 μm copper and a gold surface finish.
- Perfectly matched for use with Mosconi DSPs.

POWER SUPPLY

Supply voltage	10–16 V
DC-DC converter topology	Unregulated push-pull, 50 kHz
On-board fuse	1 × 80 A
Standby current	< 2 mA
Overall efficiency	> 65%

OUTPUT

RMS output power at 4 Ω	120 W × 4 (52.7 A)
RMS output power at 2 Ω	160 W × 4 (88 A)
Bridged RMS power at 4 Ω	320 W × 2 (88 A)

Current draw shown in parentheses.

SIGNAL INPUT

Low-level input sensitivity	1–8.75 V
Sensitivity adjustment	32 settings via DIP switch Independent for each channel
Input impedance	20 kΩ

CONNECTIONS

Power supply	Gold-plated terminal block
Speaker output	Gold-plated terminal block
Signal input	4 gold-plated RCA connectors

*SENSITIVITY SETUP

SENSITIVITY CHART				
DEFAULT SETTING 2.00V ON 1 2 3 4 5				
1.00	3.00	6.00		
1.25	3.25	6.25		
1.50	3.50	6.50		
1.75	3.75	6.75		
2.00	4.00	7.00		
2.25	4.25	7.25		
2.50	4.50	7.50		
2.75	4.75	7.75		
	5.00	8.00		
	5.25	8.25		
	5.50	8.50		
	5.75	8.75		

CEA-2006-A SPECIFICATIONS

Rated output power	120 W × 4 at 14.4 V, 4 Ω, < 1% THD+N
S/N ratio	> 95 dBA (ref. 1 W at 4 Ω)

THD

THD at 4 Ω, stereo	< 0.035% (1 kHz, 90% rated power)
THD at 2 Ω, stereo	< 0.04% (1 kHz, 90% rated power)

OTHER ELECTRICAL CHARACTERISTICS

Mute delay	3 s
Secondary voltages (VDD / SERV / DRIVE)	±38.2 / ±13.3 / ±12.5 V
Channel bias	0.15 A per trimmer
Idle current (no signal, 14.4 V)	0.86 A
Thermal shutdown current	140 mA
Battery-to-secondary ground decoupling	1 kΩ
Battery-to-chassis ground decoupling	100 mA PTC (approx. 7 Ω)
Bandwidth (–3 dB at 1 W)	< 5 Hz–135 kHz
S/N ratio (10 Hz–22 kHz, ref. rated power)	116 dB (A-weighted)
Equivalent input noise (10 Hz–22 kHz)	< 32 μV (A-weighted)
Channel separation (ref. 10 W)	> 45 dB
Fan on/off temperature	50 / 45 °C
Thermal shutdown/restart	90 / 70 °C
Damping factor at 4 Ω	> 102
Start-stop operation	Down to 7.5 V for up to 300 ms
Microcontroller	Atmel processor

PCB

Base material	FR4 (135 °C)
Solder mask	Matte black
Number of layers	2
Copper thickness	70 μm
Surface finish	Gold

APPEARANCE

Dimensions	235 × 205 × 55 mm
Weight	2.4 kg
Finish	Black / Titanium